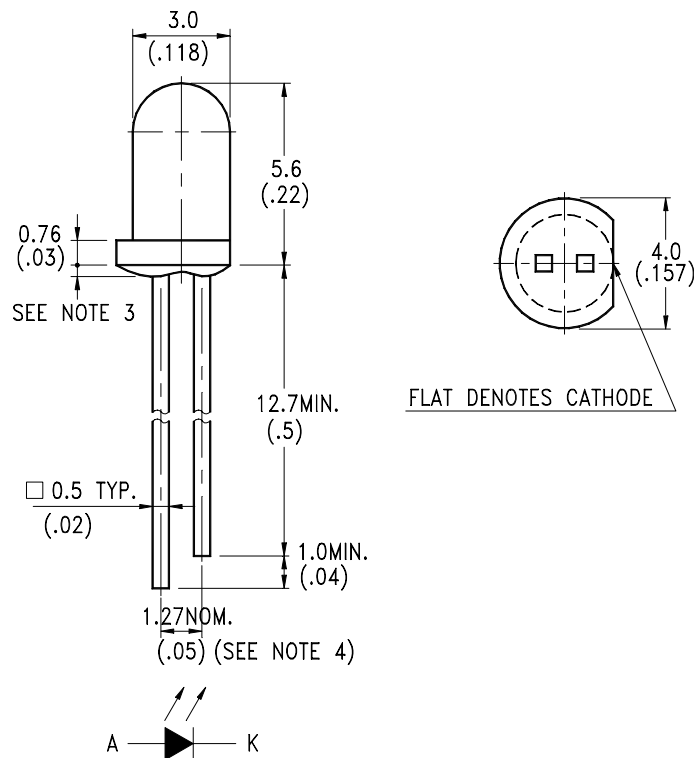


FEATURES

- * SELECTED TO SPECIFIC ON-LINE INTENSITY AND RADIANT INTENSITY RANGES
- * LOW COST MINIATURE PLASTIC END LOOKING PACKAGE
- * MECHANICALLY AND SPECTRALLY MATCHED TO THE LTR-4206 SERIES OF PHOTOTRANSISTOR
- * THE LTE-209 SERIES ARE MADE WITH GALLIUM ALUMINUM ARSENIDE WINDOW LAYER ON GALLIUM ARSENIDE INFRARED EMITTING DIODES

PACKAGE DIMENSIONS



NOTES:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25\text{mm}(.010")$ unless otherwise noted.
3. Protruded resin under flange is 1.0mm(.039") max.
4. Lead spacing is measured where the leads emerge from the package.
5. Specifications are subject to change without notice.

ABSOLUTE MAXIMUM RATINGS AT T_A=25°C

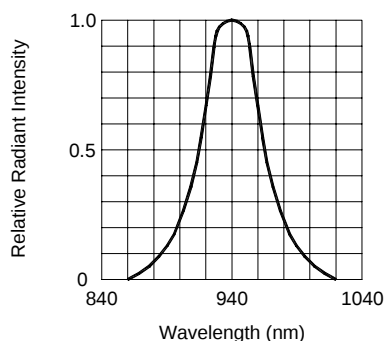
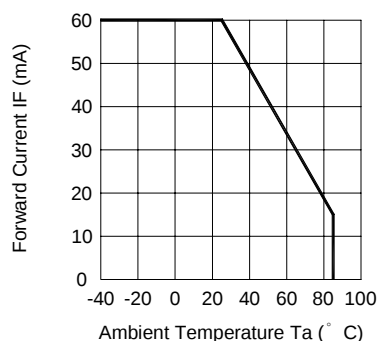
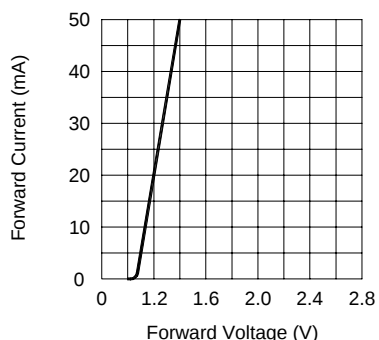
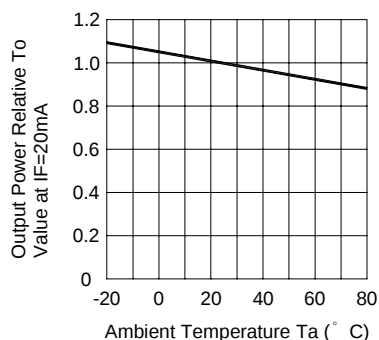
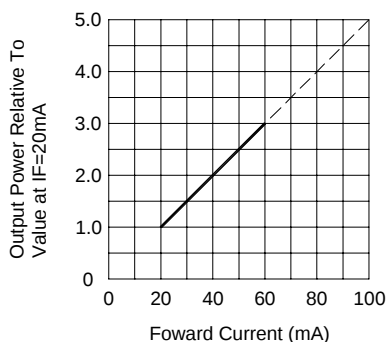
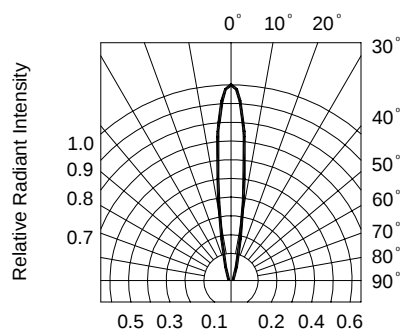
PARAMETER	MAXIMUM RATING	UNIT
Power Dissipation	90	mW
Peak Forward Current (300pps, 10 μ s pulse)	1	A
Continuous Forward Current	60	mA
Reverse Voltage	5	V
Operating Temperature Range	-40°C to + 85°C	
Storage Temperature Range	-55°C to + 100°C	
Lead Soldering Temperature [1.6mm(.063") From Body]	260°C for 5 Seconds	

ELECTRICAL OPTICAL CHARACTERISTICS AT T_A=25°C

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Aperture Radiant Incidence	E _e	0.184			mW/cm ²	I _F = 20mA
Radiant Intensity	I _E	1.383			mW/sr	I _F = 20mA
Peak Emission Wavelength	λ_{Peak}		940		nm	I _F = 20mA
Spectral Line Half-Width	$\Delta \lambda$		50		nm	I _F = 20mA
Forward Voltage	V _F		1.2	1.6	V	I _F = 20mA
Reverse Current	I _R			100	μ A	V _R = 5V
Viewing Angle (See FIG.6)	2 $\theta_{1/2}$		16		deg.	

TYPICAL ELECTRICAL / OPTICAL CHARACTERISTICS CURVES

(25°C Ambient Temperature Unless Otherwise Noted)


FIG.1 SPECTRAL DISTRIBUTION

FIG.2 FORWARD CURRENT VS. AMBIENT TEMPERATURE

FIG.3 FORWARD CURRENT VS. FORWARD VOLTAGE

FIG.4 RELATIVE RADIANT INTENSITY VS. AMBIENT TEMPERATURE

FIG.5 RELATIVE RADIANT INTENSITY VS. FORWARD CURRENT

FIG.6 RADIATION DIAGRAM